

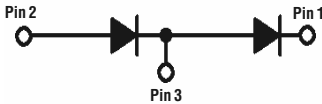


Data Sheet

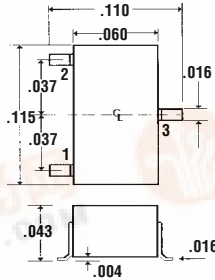
200 mW EPITAXIAL PLANAR DIODES

FMBBAV99

Description



Mechanical Dimensions



Features

- PLANAR PROCESS
- 200 mW POWER DISSIPATION
- INDUSTRY STANDARD SOT-23 PACKAGE
- MEETS UL SPECIFICATION 94V-0

Electrical Characteristics @ 25°C.		FMBBAV99	Units
Maximum Ratings		FMBBAV99	
Peak Reverse Voltage... V_{RM}		85	Volts
RMS Reverse Voltage... $V_{R(rms)}$		75	Volts
Average Forward Rectified Current... I_o		215	mAmps
Non-Repetitive Peak Forward Surge Current... I_{FSM}		4.0	Amps
Forward Voltage... V_F @ $I_F = 100$ mA		1.0	Volts
DC Reverse Current... I_R @ $V_R = 70V$		50	μ Amps
Power Dissipation... P_D		250	mW
Typical Junction Capacitance... C_j		1.5	pF
Reverse Recovery Time... t_{RR}		4.0	nS
Operating Temperature Range... T_J		-25 to 85	°C
Storage Temperature Range... T_{STRG}		-65 to 150	°C

Device Under Test

